



ABSTRACT OF THE DISCLOSURE

A plating method according to the present invention is capable of plating a substrate with a plated film of a metal such as copper or the like with high adhesion to a seed layer without producing voids in the plated film at a high throughput, not only in recesses having a large width and a small aspect ratio, but also in recesses having a small width and a large aspect ratio, even when relatively narrow recesses and relatively broad recesses are co-present in the substrate. The plating method is performed by preparing a substrate having a relatively narrow recess and a relatively broad recess defined in a surface thereof, performing a first plating process under plating conditions for filling a metal in the narrow recess, and then performing a second plating process under plating conditions for filling a metal in the broad recess.